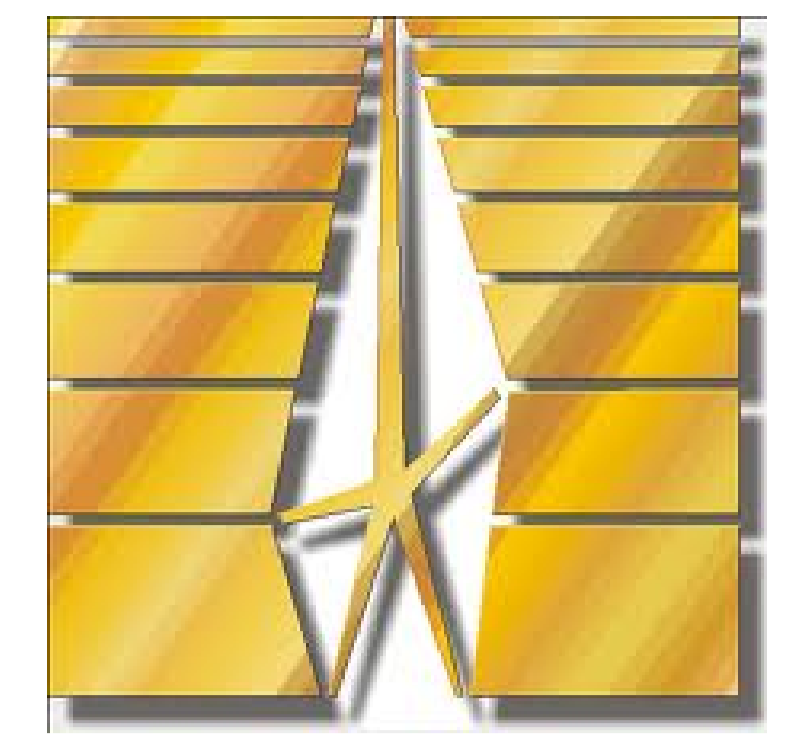


Domains in zero resistance states

Ivan Dmitriev (KIT & Ioffe Institute),

Maxim Khodas (University of Iowa), Alexander Mirlin, Dmitry Polyakov (KIT)



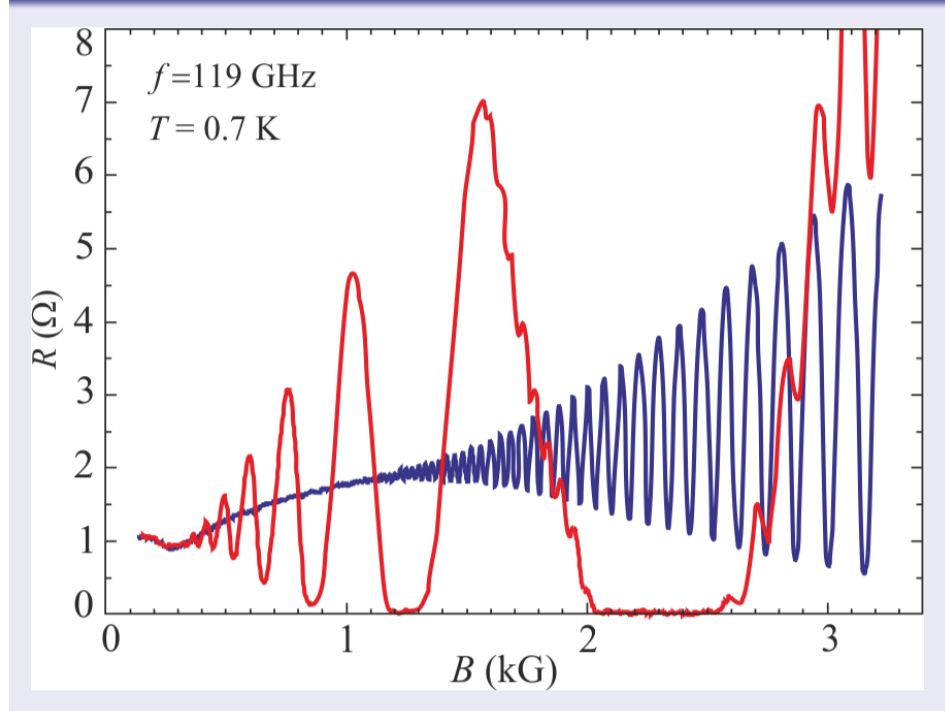
Microwave Induced Resistance Oscillations (MIRO) and associated Zero Resistance States (ZRS)

Nonequilibrium phenomena in high Landau levels

2001-present: Discovery of integer and fractional microwave-induced resistance oscillations, zero-resistance states in semiconductor quantum Hall systems and on electrons on surface of liquid He, magnetooscillations induced by strong dc current and resonant interaction with acoustic phonons, photovoltaic effects...

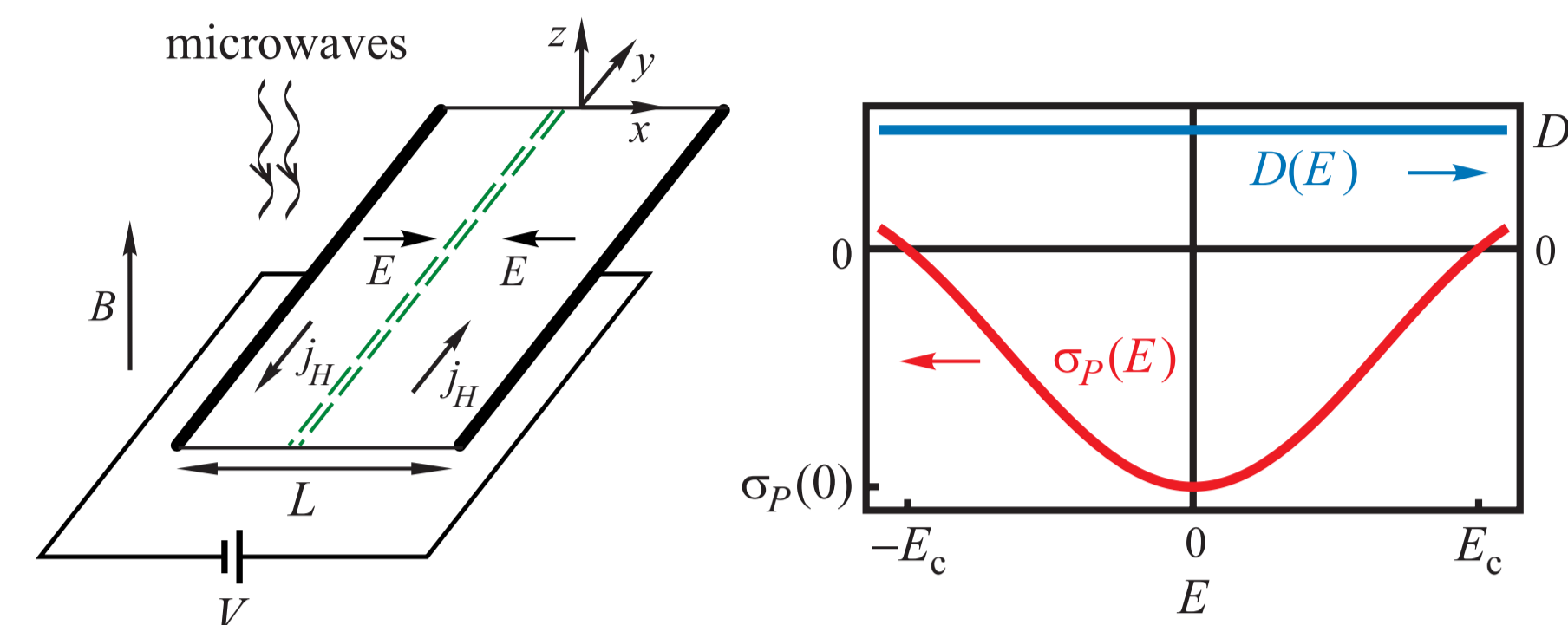
Review: Dmitriev, Mirlin, Polyakov, Zudov, *Rev. Mod. Phys.* **84**, 1709 (2012)

Experiments: MIRO & ZRS



ZRS: Mani, Smet, von Klitzing, Narayanamurti, Johnson, Umansky'02, Zudov, Du, Pfeiffer, West'03, Dorozhkin'03, Willett, Pfeiffer, West'04...
MIRO: Zudov, Du, Simmons, Reno'01, Ye, Tsui, Simmons, Wendt, Vawter, Reno'01,...

1D model of the domain state in ZRS



Negative absolute conductivity of homogeneous state, $j \cdot E < 0$

⇒ Electrical instability: Translational symmetry spontaneously broken
⇒ Electric domains ≡ Spontaneously formed inhomogeneous state

Step 1: Domain solution in infinite system

- Solve $j = 0$ with boundary conditions $E_{k \rightarrow \pm\infty} = \pm E_c$
- Take $\sigma(E) = \sigma(0) \frac{\sin \pi E / E_c}{\pi E / E_c}$, $\sigma(0) < 0$

$$\sigma(E) E(x) + D \partial_x \int \frac{\epsilon dx' E(x')}{2\pi^2 x - x'} = 0 \Rightarrow -\sin \frac{\pi E}{E_c} + \lambda \partial_x \int \frac{dx' E(x')}{x - x'} = 0$$

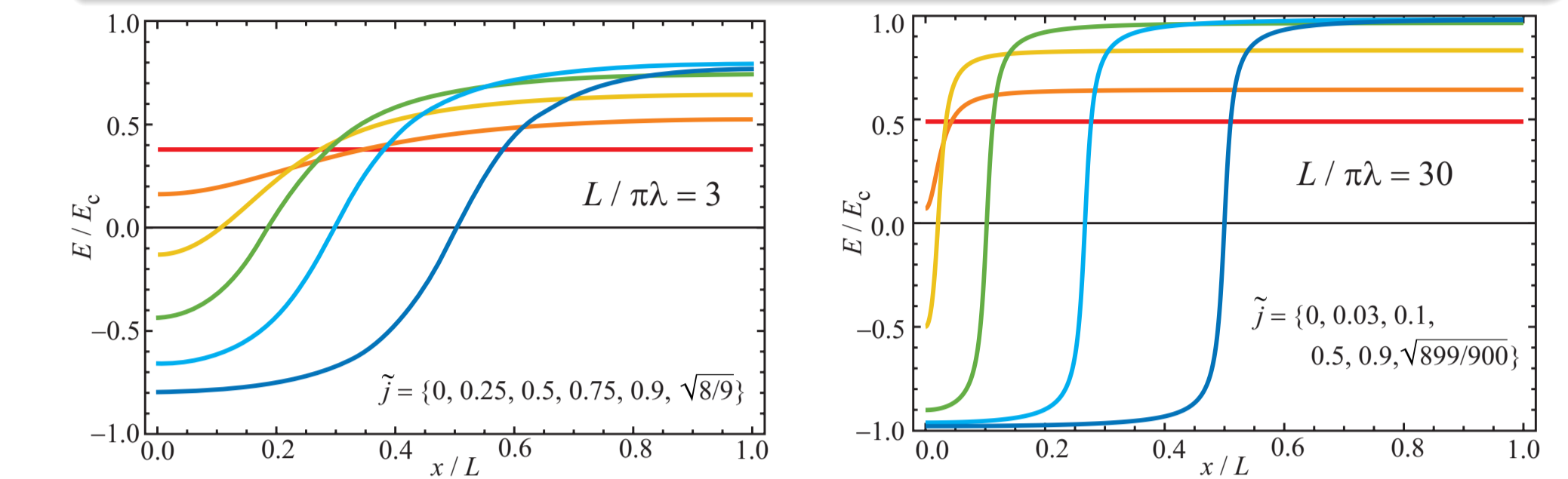
$$\text{Solution: } \frac{E}{E_c} = \frac{2}{\pi} \arctan \frac{x}{\lambda}, \quad \lambda = \frac{\epsilon D}{2\pi |\sigma(0)|}$$

Nonequilibrium screening length λ :

- The only spatial scale, width of domain wall
- Diverges at $\sigma(0) \rightarrow 0 \Rightarrow$ critical parameter
- reduces to $\lambda_{TF} = \frac{\epsilon}{2m e^2}$ in equilibrium

Step 3: Domain solution in a biased 2D stripe

- Solve $\sin \frac{\pi E}{E_c} - \lambda \partial_x \int \frac{dx' E(x')}{E_c x - x'} = \tilde{j}$; (Anti)dissipative current $\tilde{j} = \frac{\pi j}{\sigma(0) E_c}$



$$\frac{E}{E_c} = \frac{2}{\pi} \arctan \left(l^2 \tilde{j} \sqrt{1 - \tilde{j}^2} - l \sqrt{1 - l^2 - \tilde{j}^2} \sqrt{1 + l^2 \tilde{j}^2} \cos \frac{\pi x}{L} \right) - \frac{1}{\pi} \arcsin \tilde{j}, \quad l = \frac{L}{\pi \lambda}$$

$$\text{Full solution: } \Psi \equiv \frac{\pi}{2 E_c} E + i \frac{\pi^2}{\epsilon E_c} \rho = i \ln \frac{\cosh(\xi - i w)}{\sinh \xi} - \frac{1}{2} \arcsin \tilde{j}, \quad |\tilde{j}| \leq \sqrt{1 - l^2}$$

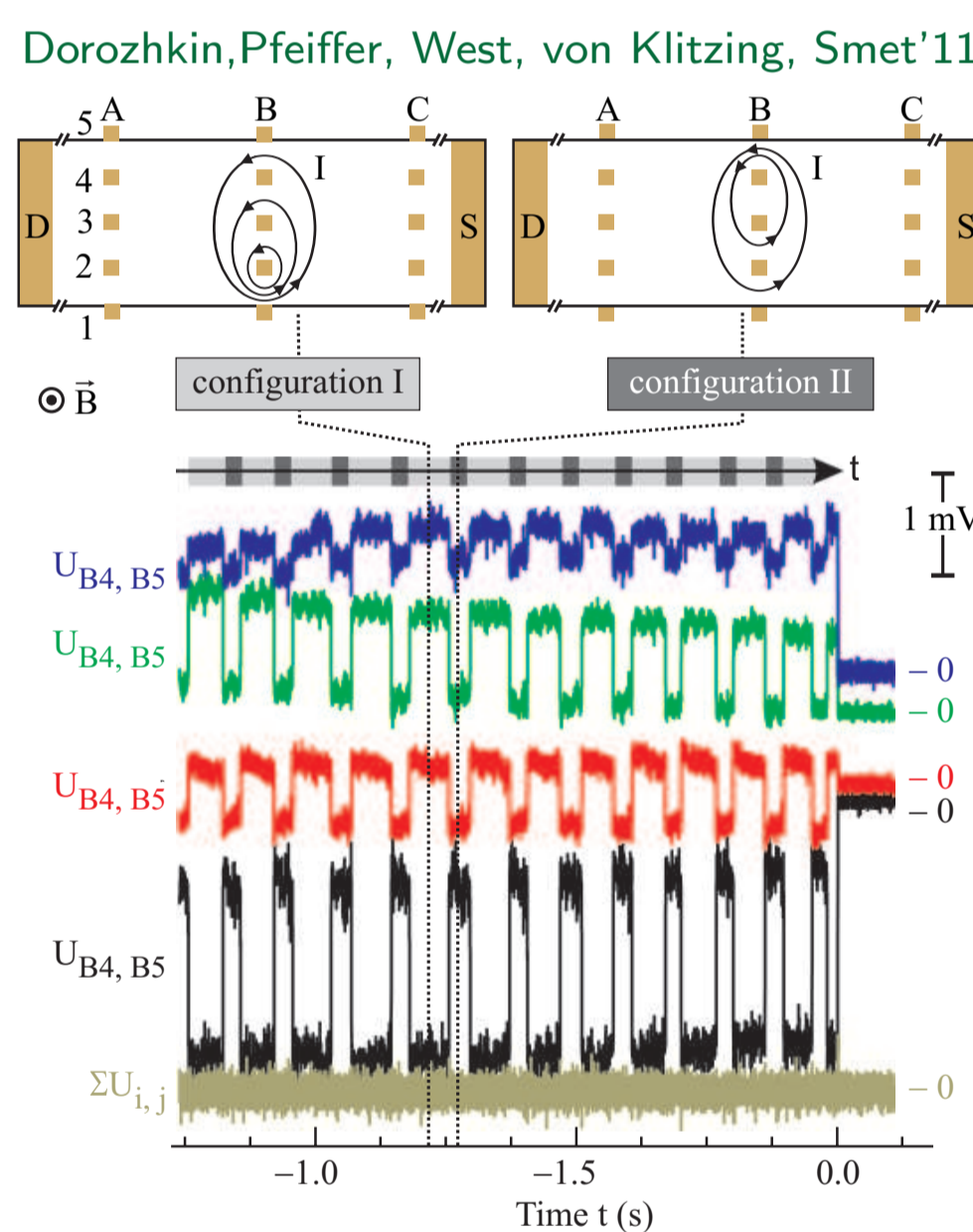
where $2\xi = i\pi(x/L - 1/2) + iw + \beta$, $w = \arctan(\tilde{j}l)$, $\beta = \text{arcoth}(l\sqrt{1 - \tilde{j}^2})$

Direct evidence for static domains in ZRS?

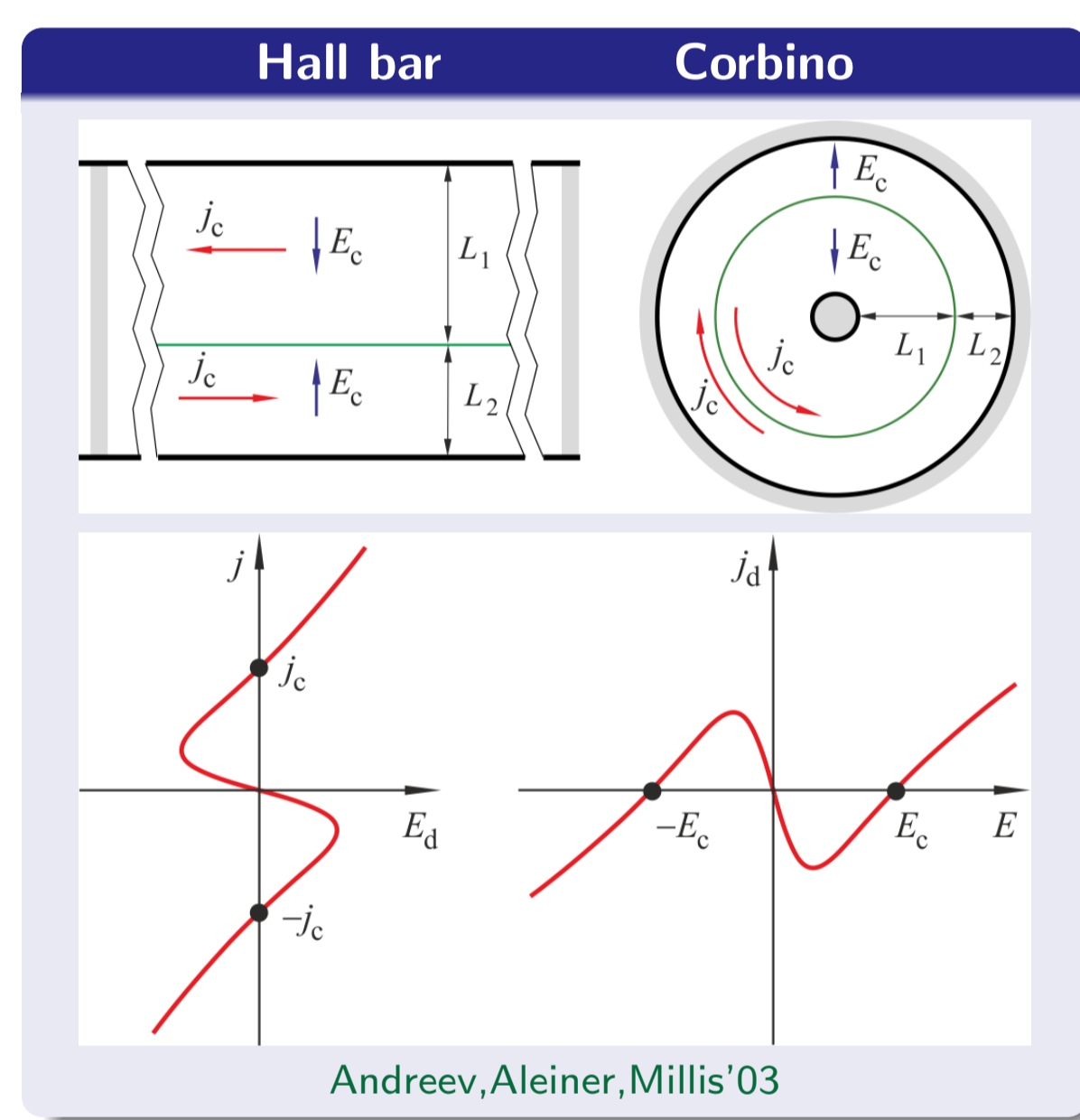
Time-resolved measurement of photovoltage signals between internal probes under continuous illumination

Random telegraph signals for Hall voltages

Interpreted as spontaneous switching between two nearly degenerate configurations of domains



Domains ⇒ zero resistance/conductance



Domains with $j_c \perp E_c = \rho_H j_c$, where $\sigma(E_c) = 0$ and $\rho_H = B/e v_F$.

External bias moves the domain wall

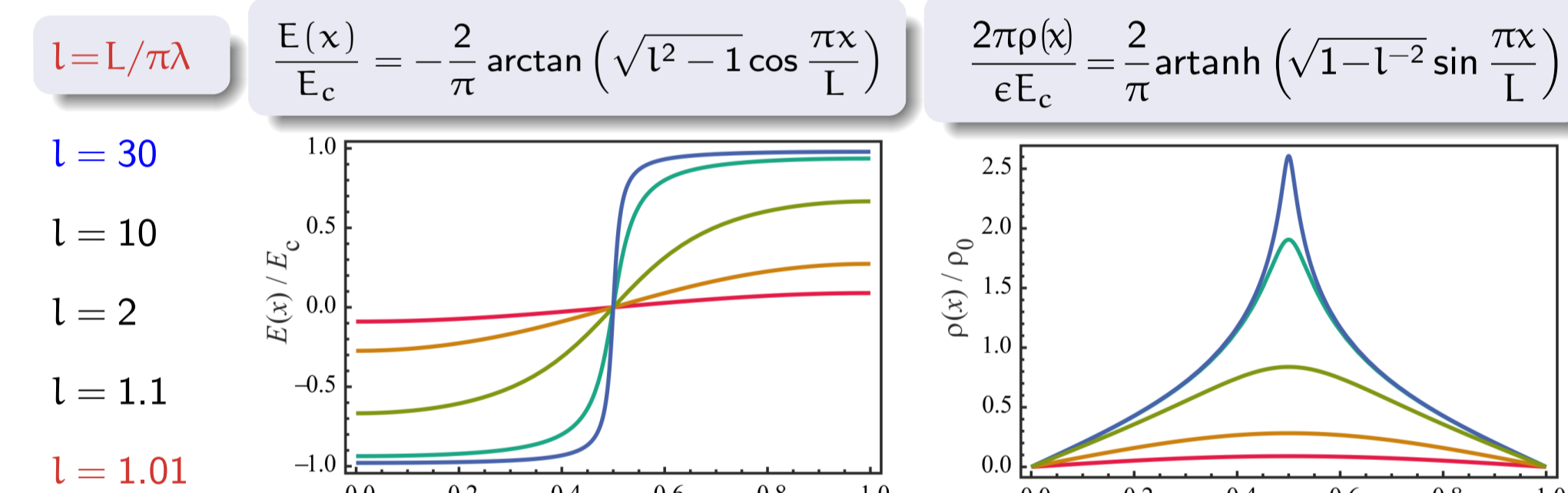
Hall bar – zero resistance state: $V = 0$ for any $I = j_c(L_1 - L_2)$

Corbino – zero conductance state: $I = 0$ for any $V = E_c(L_1 - L_2)$

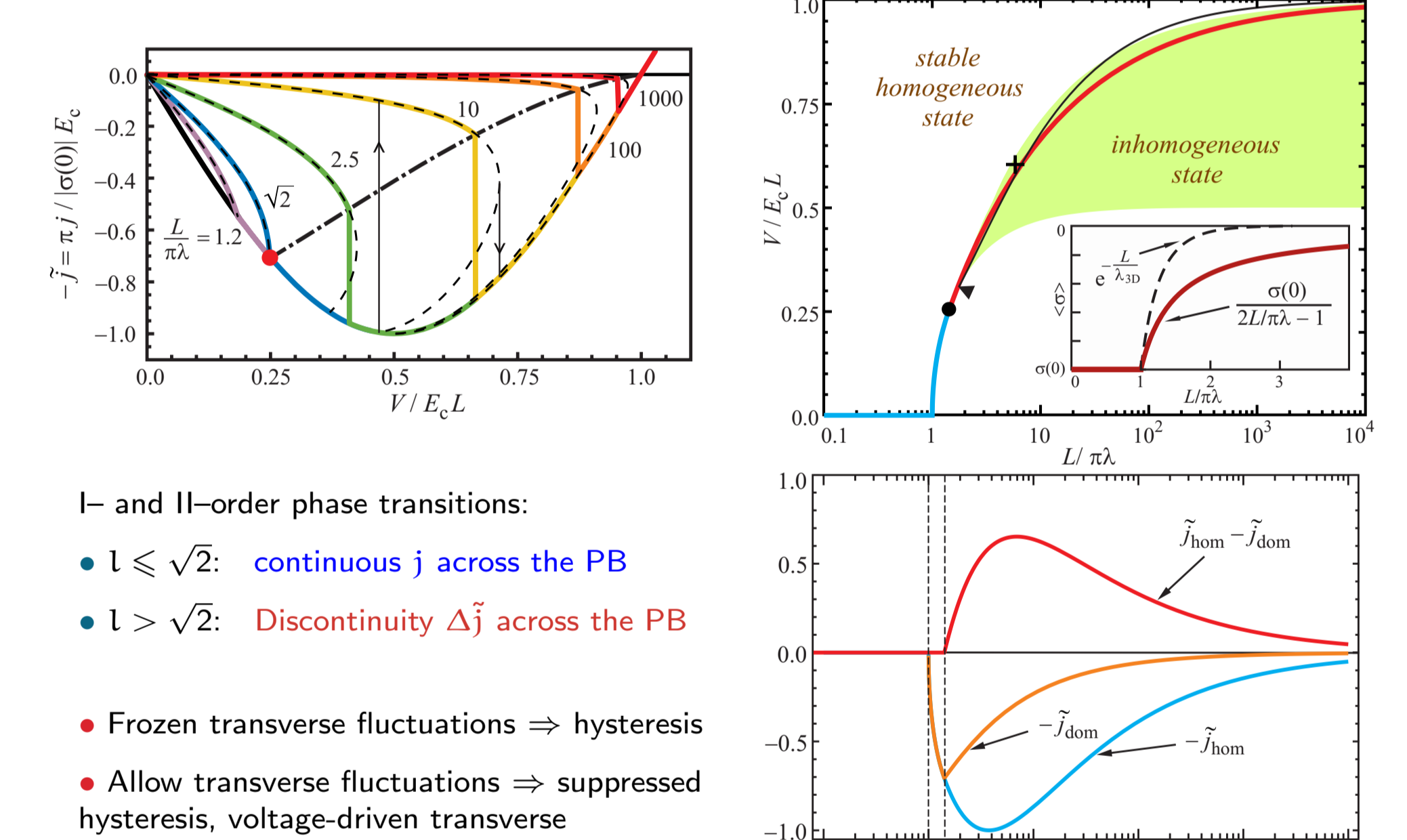
Step 2: Domain solution in unbiased finite system

Spatio-temporal fluctuations $\delta \rho(x, t) \propto e^{i q x} \psi \sin(q_x x)$: Stability $\Leftrightarrow \partial_t \ln \delta \rho(t) < 0$

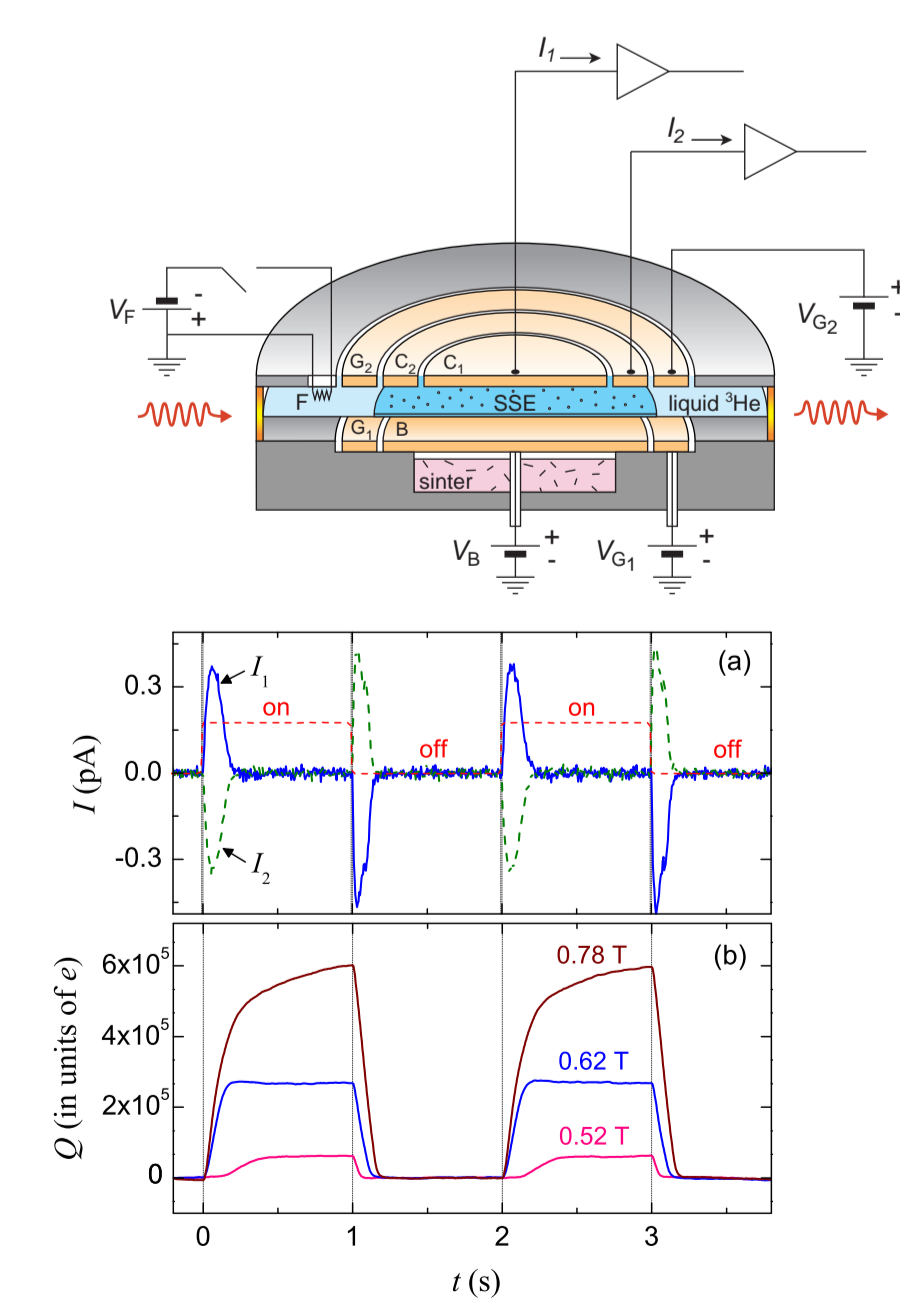
- Finite L: uniform state $\rho(x) \equiv 0$ is stable for $\sigma > -\epsilon D / 2L \Leftrightarrow l = L / \pi \lambda < 1$
- Size-dependent instability threshold! • $L \rightarrow \infty$: usual condition $\sigma > 0$
- Phenomena at $-\epsilon D / 2L < \sigma < 0$ ($0 < l < 1$) → Dorozhkin, Dmitriev, Mirlin, PRB'11



Full CVC, phase diagram, and current discontinuity



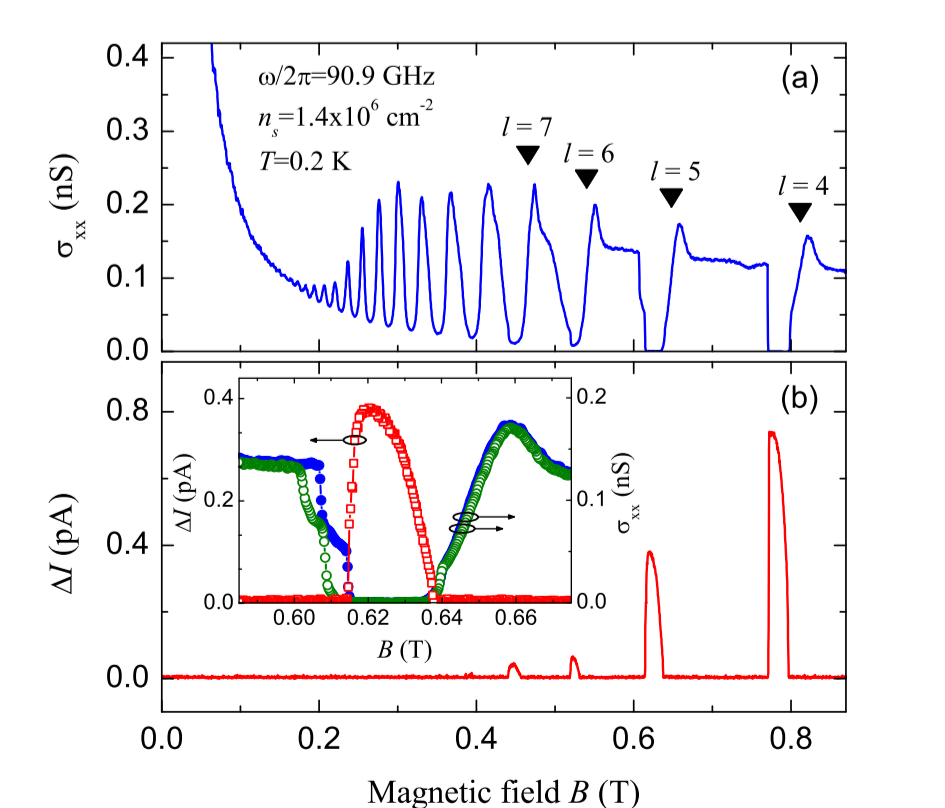
Wigner electron liquid on surface of liquid He



Konstantinov and Kono'09,10, Konstantinov, Chepelianskii, Kono'12

- Oscillations and vanishing dissipation under microwave illumination.
- Time-resolved capacitive measurement for microwaves switching on and off:

Charge transfer due to domain formation



Overview of the model: Key ingredients

2D charge density $\rho(x)$ & in-plane electric field $E(x)$

Poisson equation: $-\epsilon \Delta \Phi = 4\pi \rho \delta(z) \Rightarrow \rho(x) = - \int \frac{\epsilon dx' E(x')}{2\pi^2 x - x'}$

Continuity equation: $\partial_t \rho + \nabla \cdot j = 0$ (Static domains $\Rightarrow \partial_t \rho = 0$)

$j = \sigma(E) E - D \nabla \rho$: conductivity $\sigma(0) < 0$, diffusion coefficient $D > 0$

Einstein relation doesn't hold: $e^2 v_0 D \neq \sigma!$

Resulting self-consistent nonlinear integral equation

$$j = \sigma(E) E(x) + D \partial_x \int \frac{\epsilon dx' E(x')}{2\pi^2 x - x'} + \text{boundary conditions}$$

General approach to stability: Lyapunov functional

Lyapunov functional $\Phi = K - G$: Stable solution \equiv Global minimum of Φ

Application to ZRS (3D, limit $\lambda \ll L$): A. Auerbach, I. Finkler, B. I. Halperin, A. Yacoby'05

- Gain $G = - \int dx \int_0^{E(x)} \sigma(E') E' dE'$: $\sigma < 0 \Rightarrow$ Maximized for $|E(x)| = E_c$
- Domain walls $K = \frac{D}{2} \int dx E(x) \hat{C} E(x) \geq 0 \Rightarrow$ Minimized for $\partial_x E = 0$
- capacitance C: $\rho(x) = \hat{C} \Phi(x)$, $[\hat{C}, \partial_x] = 0 \Rightarrow \partial_x \rho = -\hat{C} E$

$$\text{Allow } E(x, t): \dot{\Phi} = \int dx [\sigma(E) E \dot{E} + D \dot{E} \hat{C} E] = \int dx [\sigma(E) E - D \partial_x \rho] \dot{E} = \int dx j \dot{E}$$

$$\text{Poisson } E = -\hat{C}^{-1} \partial_x \rho \quad \& \quad \text{Continuity } \dot{\rho} = -\partial_x j \Rightarrow \dot{E} = \hat{C}^{-1} \partial_x^2 j$$

$$\Rightarrow \dot{\Phi} = \int dx j \dot{E} = \int dx j \hat{C}^{-1} \partial_x^2 j = - \int dx (\partial_x j) \hat{C}^{-1} (\partial_x j) \leq 0$$

Summary and Outlook

Summary: Analytical model of the domain state in ZRS

- 2D electrostatics
- Evolution with system size L and external bias V
- Transverse instability at large V and L

Outlook

- Mean field: Analysis of transverse fluctuations, inclusion of contact potentials, macroscopic inhomogeneities, periodic spatial modulation etc.
- Critical behavior at the transition to ZRS: Influence of noise, nature of transition, dynamics at "zero" and finite temperature
- Domain structure in zero differential resistance states in Hall and Corbino geometries
- Domain structure in "zero admittance states" in electron liquid on surface of liquid He
- Experimental evidence of the domain formation: S. I. Dorozhkin et al., *Nature Phys.* **7**, 336 (2011); Konstantinov et al., *J. Phys. Soc. Jpn.* **81**, 093601 (2012).
- Review: I. A. Dmitriev, A. D. Mirlin, D. G. Polyakov, M. A. Zudov, *Rev. Mod. Phys.* **84**, 1709 (2012)
- Domains in "3D": A. Auerbach et al., *Phys. Rev. Lett.* **94**, 196801 (2005); I. G. Finkler and B. I. Halperin, *Phys. Rev. B* **79**, 085315 (2009); J. Alicea et al., *Phys. Rev. B* **71**, 235322 (2005); A. F. Volkov and V. V. Pavlovskii, *Phys. Rev. B* **69**, 125305 (2004)